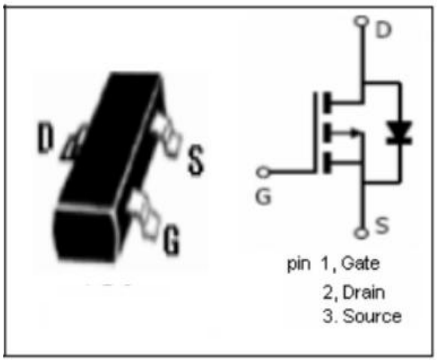
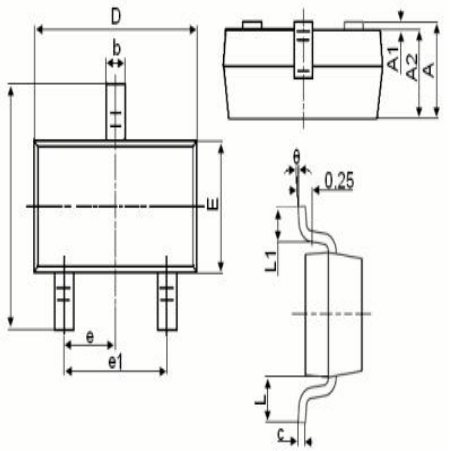
Isc P-Channel MOSFET Transistor IRLML6302

- **FEATURES**
- With SOT-23 package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



- **APPLICATIONS**
- Switching applications



- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	±12	V
I_D	Drain Current-Continuous Tc=25℃ Tc=70℃	-0.78 -0.26	A
I_{DM}	Drain Current-Single Pulsed	-4.9	A
P_D	Total Dissipation @T_C=25℃	540	mW
T_{ch}	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-a)	Channel-to-ambient thermal resistance	230	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D=-0.25mA	-20			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D=-0.25mA	-0.7		-1.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= -4.5V; I_D=-0.61A			600	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±12V;V_{DS}=0V			±0.1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-16V; V_{GS}= 0V;Tj=25℃ V_{DS}=-16V; V_{GS}= 0V;Tj=150℃			-1 -25	μA
V_{SDF}	Diode forward voltage	I_{SD}=-0.61A, V_{GS} = 0V			-1.2	V